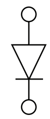
HEXFRED®
Ultrafast Soft Recovery Diode, 275 A

HALF-PAK (D-67)

Lug terminal
anode



Base
cathode

FEATURES

- Very low Q_{rr} and t_{rr}
- Lead (Pb)-free
- Designed and qualified for industrial level

RoHS
COMPLIANT

BENEFITS

- Reduced RFI and EMI
- Reduced snubbing

DESCRIPTION

HEXFRED® diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dI/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

PRODUCT SUMMARY	
I_F (maximum)	275 A
V_R	400 V
$I_{F(DC)}$ at T_C	138 A at 100 °C

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_R		400	V
Continuous forward current	I_F	T_C = 25 °C	275	A
		T_C = 100 °C	138	
Single pulse forward current	I_{FSM}	Limited by junction temperature	900	
Non-repetitive avalanche energy	E_{AS}	L = 100 µH, duty cycle limited by maximum T_J	1.4	mJ
Maximum power dissipation	P_D	T_C = 25 °C	463	W
		T_C = 100 °C	185	
Operating junction and storage temperature range	T_J, T_{Stg}		- 55 to + 150	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA		400	-	-	V
Maximum forward voltage	V_{FM}	I_F = 135 A	See fig. 1	-	1.06	1.65	
		I_F = 270 A		-	1.2	2.0	
		I_F = 135 A, T_J = 125 °C		-	0.96	1.58	
Maximum reverse leakage current	I_{RM}	T_J = 125 °C, V_R = 400 V	See fig. 2	-	-	3	mA
Junction capacitance	C_T	V_R = 200 V	See fig. 3	-	280	380	pF
Series inductance	L_S	From top of terminal hole to mounting plane		-	6.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5	t_{rr}	T_J = 25 °C	I_F = 135 A dI_F/dt = 200 A/µs V_R = 200 V	-	77	120	ns
		T_J = 125 °C		-	280	440	
Peak recovery current See fig. 6	I_{RRM}	T_J = 25 °C		-	7.5	14	A
		T_J = 125 °C		-	15	30	
Reverse recovery charge See fig. 7	Q_{rr}	T_J = 25 °C		-	150	780	nC
		T_J = 125 °C		-	2800	6300	
Peak rate of recovery current See fig. 8	$dI_{(rec)M}/dt$	T_J = 25 °C		-	350	-	A/µs
		T_J = 125 °C		-	300	-	

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T_J, T_{Stg}		- 55 to 150	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation See fig. 4	0.27	°C/W
Typical thermal resistance, case to heatsink		R_{thCS}	Mounting surface, flat, smooth and greased	0.05	
Approximate weight				30	g
				1.06	oz.
Mounting torque	minimum			3 (26.5)	N · m (lbf · in)
	maximum			4 (35.4)	
Terminal torque	minimum			3.4 (30)	
	maximum			5 (44.2)	
Case style			HALF-PAK module		

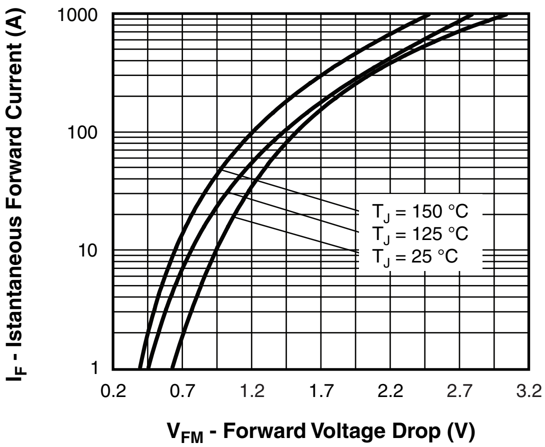


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

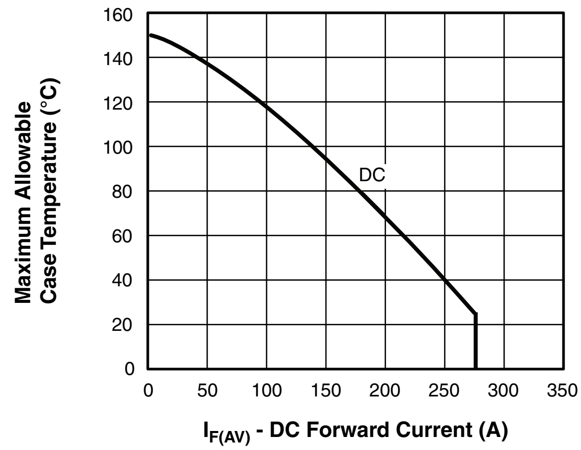


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current

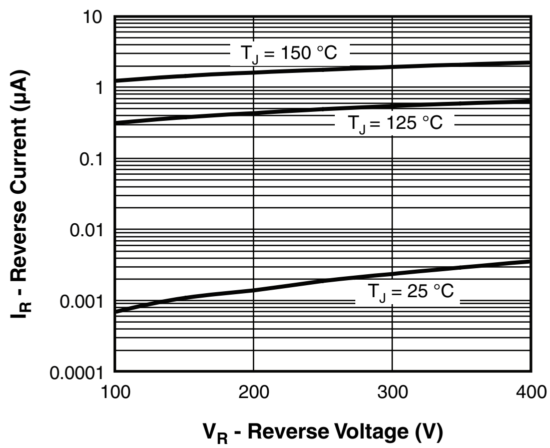


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

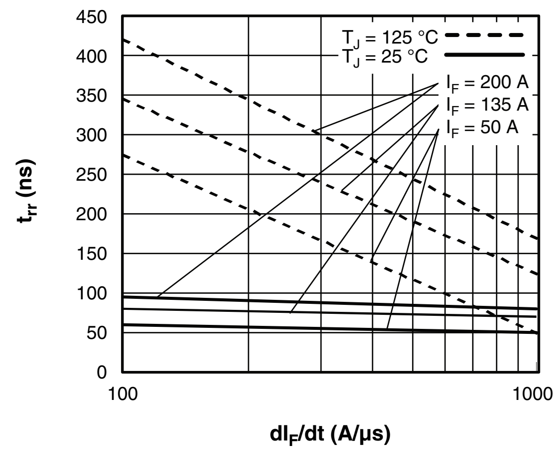


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

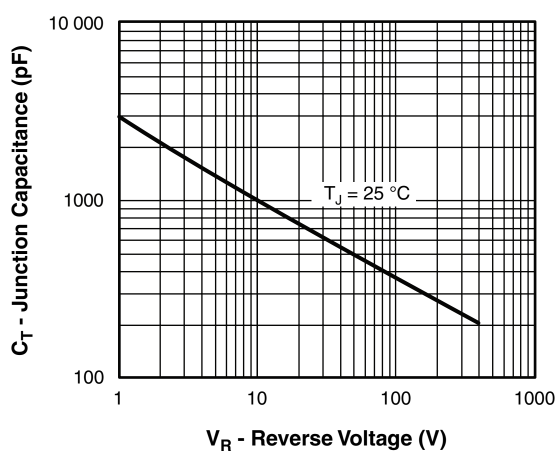


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

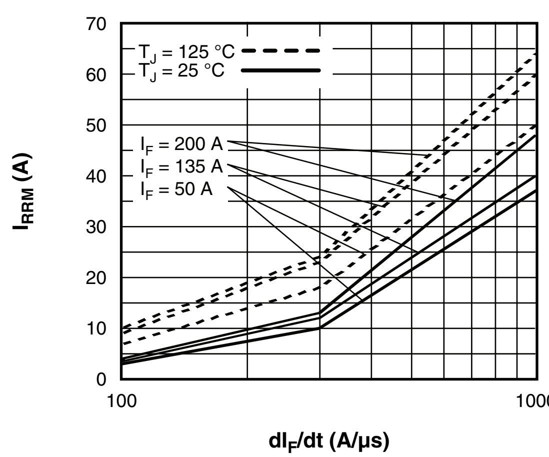


Fig. 6 - Typical Recovery Current vs. dI_F/dt

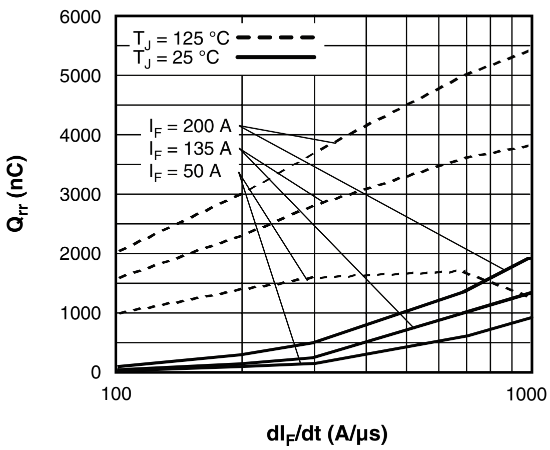


Fig. 7 - Typical Stored Charge vs. dI_F/dt

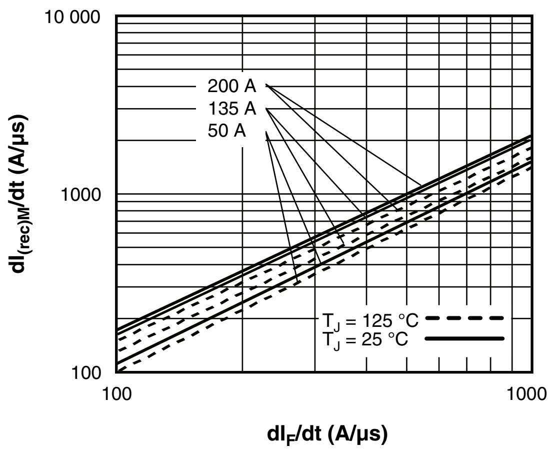


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

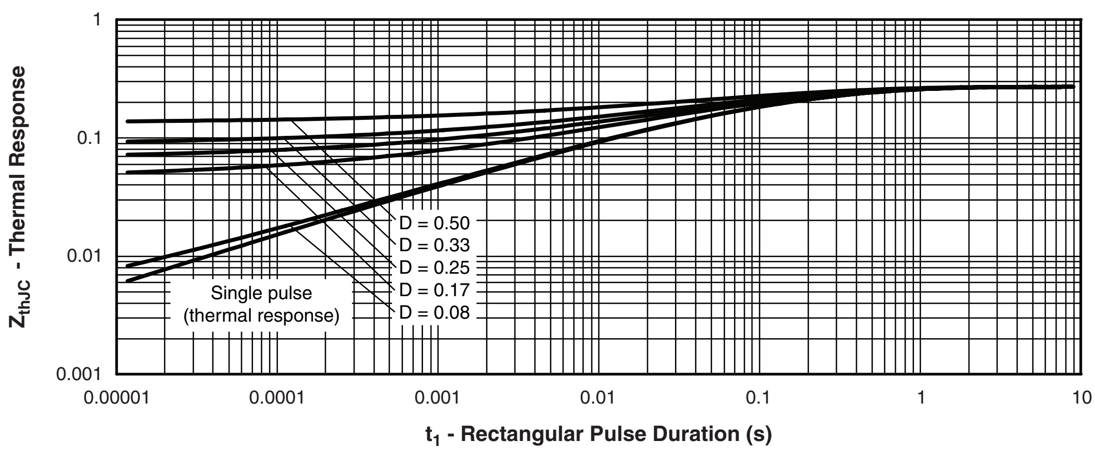


Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics

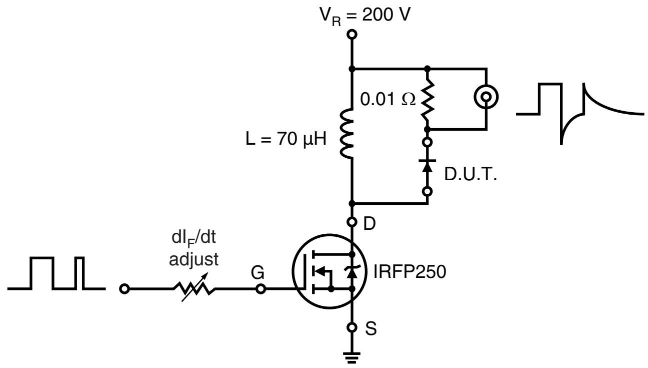
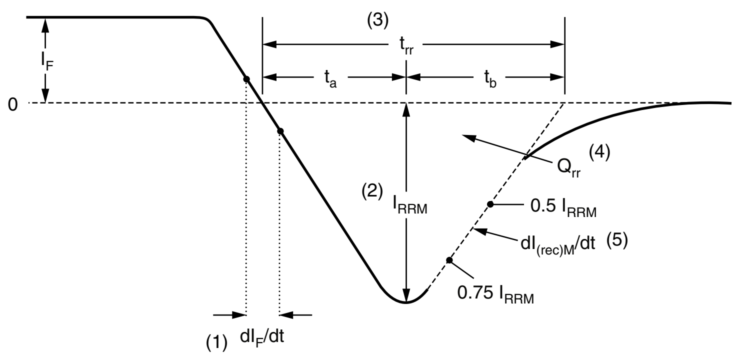


Fig. 10 - Reverse Recovery Parameter Test Circuit



(1) dI_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}$/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

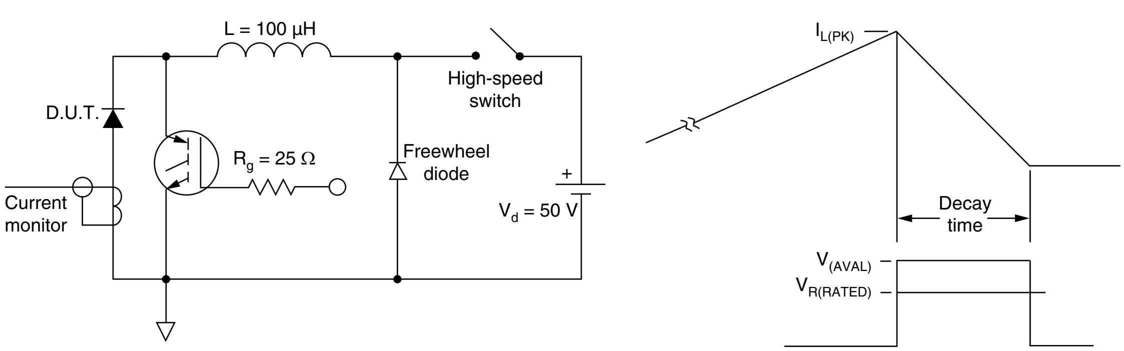


Fig. 12 - Avalanche Test Circuit and Waveforms

ORDERING INFORMATION TABLE

Device code	HFA	135	N	H	40	PbF
	1	2	3	4	5	6

1 - HEXFRED® family
2 - Average current rating
3 - N = Not isolated
4 - H = HALF-PAK
5 - Voltage rating (400 V)
6 - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95020

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